



IRFM120ATF Information

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Part Number IRFM120ATF

ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor Products
Transistors - FETs, MOSFETs - SingleDescriptionMOSFET N-CH 100V 2.3A SOT-223

Package TO-261-4, TO-261AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRFM120ATF Specifications

Manufacturer Part Number IRFM120ATF Manufacturer Fairchild/ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-261-4, TO-261AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 2.3A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 22nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 480pF @ 25V Vgs (Max) E 2V FET Feature - Power Dissipation (Max) 2.4W (Ta) Rds On (Max) @ Id, Vgs 200 mOhm @ 1.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223-4 Package / Case TO-261-4, TO-261AA		
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Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 2.3A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 22nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 480pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.4W (Ta) Rds On (Max) @ Id, Vgs 200 mOhm @ 1.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223-4 Package / Case TO-261-4, TO-261AA		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C2.3A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs22nC @ 10VInput Capacitance (Ciss) (Max) @ Vds480pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.4W (Ta)Rds On (Max) @ Id, Vgs200 mOhm @ 1.15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223-4Package / CaseTO-261-4, TO-261AA	Package	TO-261-4, TO-261AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C2.3A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs22nC @ 10VInput Capacitance (Ciss) (Max) @ Vds480pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.4W (Ta)Rds On (Max) @ Id, Vgs200 mOhm @ 1.15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223-4Package / CaseTO-261-4, TO-261AA	Series	-
Drain to Source Voltage (Vdss)100 VCurrent - Continuous Drain (Id) @ 25°C2.3A (Ta)Drive Voltage (Max Rds On, Min Rds On)10 VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs22nC @ 10 VInput Capacitance (Ciss) (Max) @ Vds480pF @ 25 VVgs (Max)±20 VFET Feature-Power Dissipation (Max)2.4W (Ta)Rds On (Max) @ Id, Vgs200 mOhm @ 1.15A, 10 VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223-4Package / CaseTO-261-4, TO-261AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C2.3A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs22nC @ 10VInput Capacitance (Ciss) (Max) @ Vds480pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.4W (Ta)Rds On (Max) @ Id, Vgs200 mOhm @ 1.15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223-4Package / CaseTO-261-4, TO-261AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs22nC @ 10VInput Capacitance (Ciss) (Max) @ Vds480pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.4W (Ta)Rds On (Max) @ Id, Vgs200 mOhm @ 1.15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223-4Package / CaseTO-261-4, TO-261AA	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Operating Type Surface Mount Supplier Device Package Package / Case Avo Q 250μA 480 pF @ 25V 50V FET Feature	Current - Continuous Drain (Id) @ 25°C	2.3A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 480pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 200 mOhm @ 1.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223-4 Package / Case TO-261-4, TO-261AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 480pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 200 mOhm @ 1.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223-4 Package / Case TO-261-4, TO-261AA	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)2.4W (Ta)Rds On (Max) @ Id, Vgs200 mOhm @ 1.15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223-4Package / CaseTO-261-4, TO-261AA	Gate Charge (Qg) (Max) @ Vgs	22nC @ 10V
FET Feature - Power Dissipation (Max) 2.4W (Ta) Rds On (Max) @ Id, Vgs 200 mOhm @ 1.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223-4 Package / Case TO-261-4, TO-261AA	Input Capacitance (Ciss) (Max) @ Vds	480pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 200 mOhm @ 1.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223-4 Package / Case TO-261-4, TO-261AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs200 mOhm @ 1.15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223-4Package / CaseTO-261-4, TO-261AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223-4 Package / Case TO-261-4, TO-261AA	Power Dissipation (Max)	2.4W (Ta)
Mounting Type Surface Mount Supplier Device Package SOT-223-4 Package / Case TO-261-4, TO-261AA	Rds On (Max) @ Id, Vgs	200 mOhm @ 1.15A, 10V
Supplier Device Package SOT-223-4 Package / Case TO-261-4, TO-261AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-261-4, TO-261AA	Mounting Type	Surface Mount
	Supplier Device Package	SOT-223-4
Report errors?	Package / Case	TO-261-4, TO-261AA
		Report errors?

IRFM120ATF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFM120ATF Payment Methods



















IRFM120ATF Shipping Methods













If you have any question about IRFM120ATF, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com